

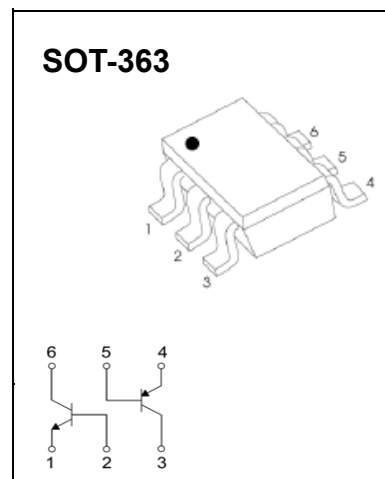
Plastic-Encapsulate Transistors

DUAL TRANSISTOR (NPN+PNP)

FEATURES

- Epitaxial Die Construction
- Two isolated NPN/PNP(BC846W+BC856W) Transistors in one package

MAKING: BB



MAXIMUM RATINGS TR1 (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Units
V _{CB0}	Collector-Base Voltage	80	V
V _{CEO}	Collector-Emitter Voltage	65	V
V _{EBO}	Emitter-Base Voltage	6	V
I _C	Collector Current –Continuous	0.1	A
P _C	Collector Power Dissipation	200	mW
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55-150	°C

CHARACTERISTICS of TR1 (NPN Transistor) (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =10μA, I _E =0	80			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =10mA, I _B =0	65			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =1μA, I _C =0	6			V
Collector cut-off current	I _{CBO}	V _{CB} =30V, I _E =0			15	nA
Emitter cut-off current	I _{EBO}	V _{EB} =5V, I _C =0			15	nA
DC current gain	h _{FE}	V _{CE} =5V, I _C =2mA	200		450	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =10mA, I _B =0.5mA			0.25	V
	V _{CE(sat)}	I _C =100mA, I _B =5mA			0.6	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =10mA, I _B =0.5mA		0.7		V
	V _{BE(sat)}	I _C =100mA, I _B =5mA		0.9		V
Base-emitter voltage	V _{BE(on)}	V _{CE} =5V, I _C =2mA	0.58		0.7	V
	V _{BE(on)}	V _{CE} =5V, I _C =10mA			0.72	V
Collector output capacitance	C _{ob}	V _{CB} =10V, I _E =0, f=1MHz			6.0	pF
Transition frequency	f _T	V _{CE} =5V, I _C =10mA, f=100MHz	100			MHz
Noise figure	NF	V _{CE} =5V, I _C =0.2mA, f=1kHz, R _g =2KΩ, Δf=200Hz			10	dB

MAXIMUM RATINGS TR2 (T_a=25°C unless otherwise noted)

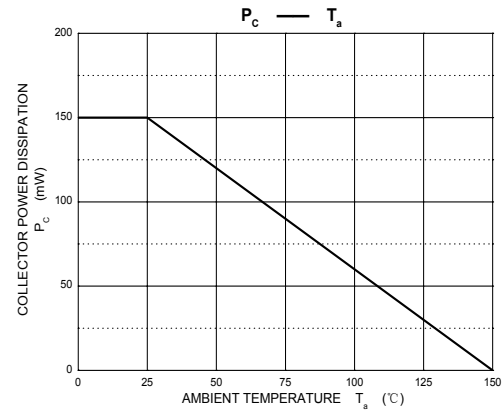
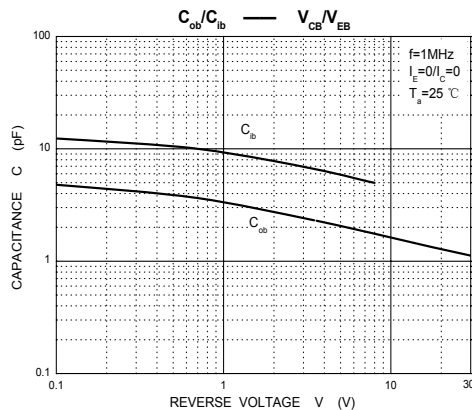
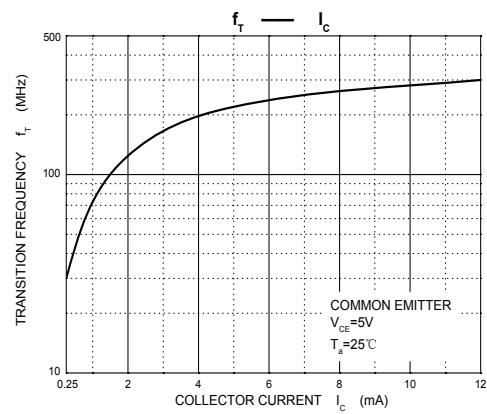
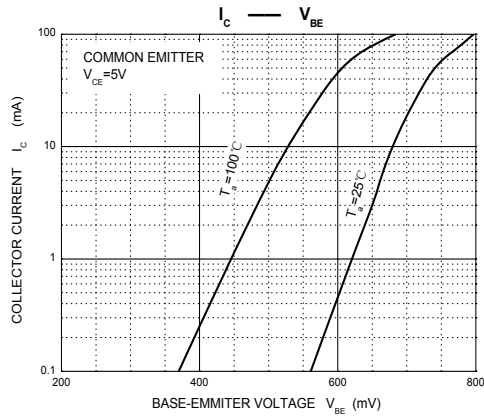
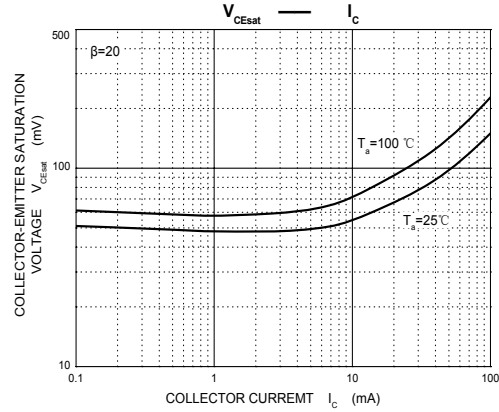
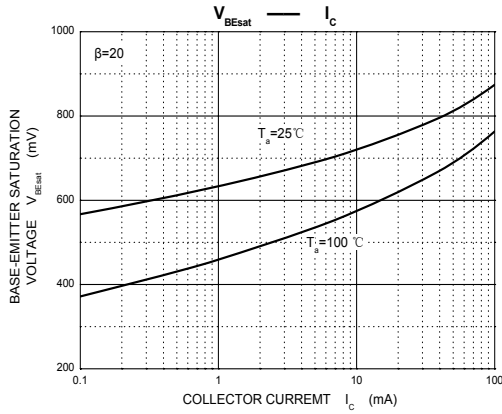
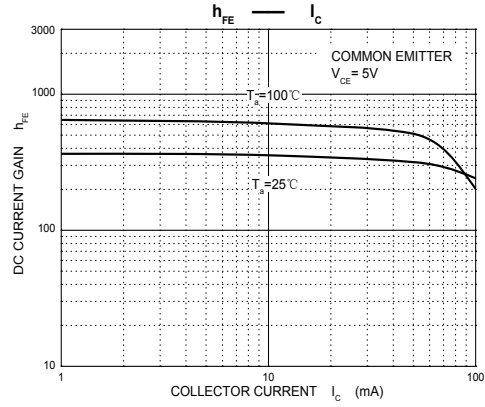
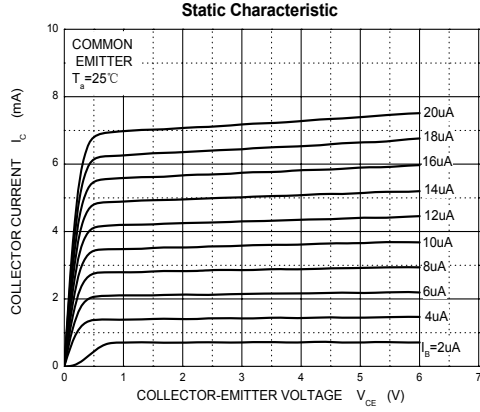
Symbol	Parameter	Value	Units
V _{CB0}	Collector-Base Voltage	-80	V
V _{CEO}	Collector-Emitter Voltage	-65	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _c	Collector Current –Continuous	-0.1	A
P _{C*}	Collector Power Dissipation	200	mW
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55-150	°C

CHARACTERISTICS of TR2 (PNP Transistor) (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-10μA, I _E =0	-80			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-10mA, I _B =0	-65			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-1μA, I _C =0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} =-30V, I _E =0			-15	nA
Emitter cut-off current	I _{EBO}	V _{EB} =-5V, I _C =0			-15	nA
DC current gain	h _{FE1}	V _{CE} =-5V, I _C =-2mA	220		475	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-10mA, I _B =-0.5mA			-0.3	V
	V _{CE(sat)}	I _C =-100mA, I _B =-5mA			-0.65	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =-10mA, I _B =-0.5mA		-0.7		V
	V _{BE(sat)}	I _C =-100mA, I _B =-5mA			-0.95	V
Base-emitter voltage	V _{BE(on)}	V _{CE} =-5V, I _C =-2mA	-0.6		-0.75	V
	V _{BE(on)}	V _{CE} =-5V, I _C =-10mA			-0.82	V
Collector output capacitance	C _{ob}	V _{CB} =-10V, I _E =0, f=1MHz			4.5	pF
Transition frequency	f _T	V _{CE} =-5V, I _C =-10mA, f=100MHz	100			MHz
Noise figure	NF	V _{CE} =-5V, I _c =-0.2mA, f=1kHz, R _g =2KΩ, Δf=200Hz			10	dB

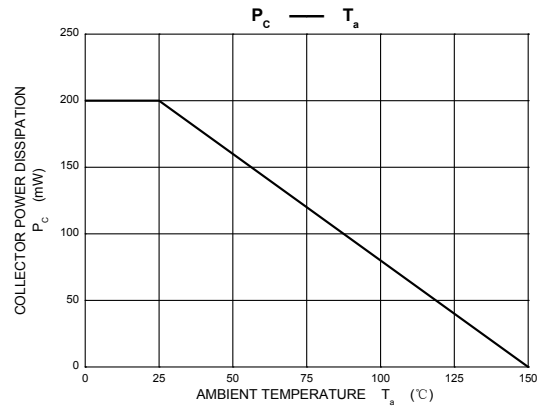
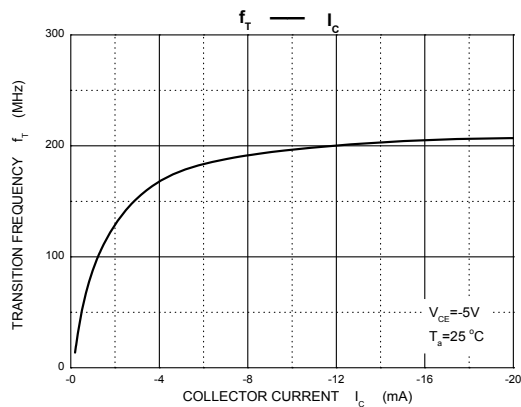
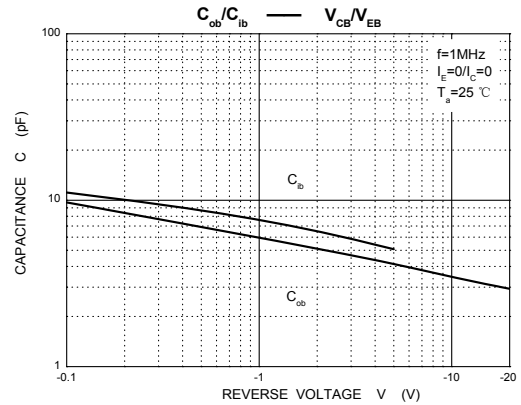
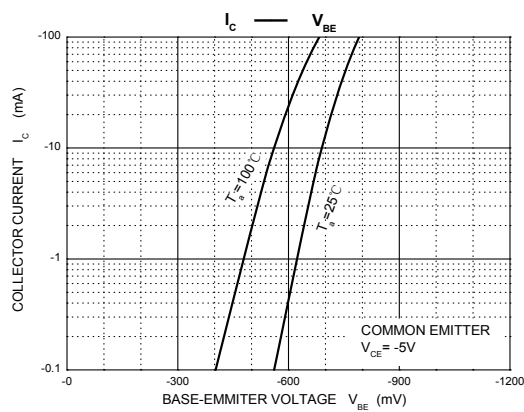
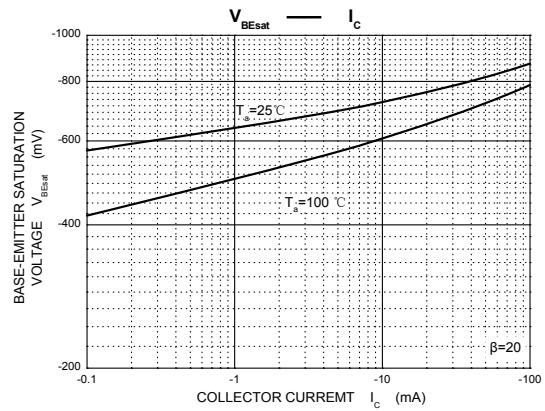
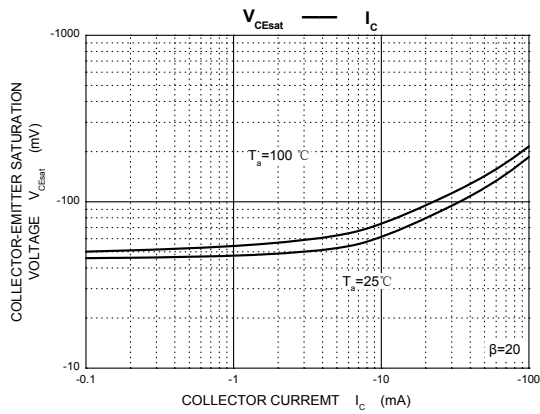
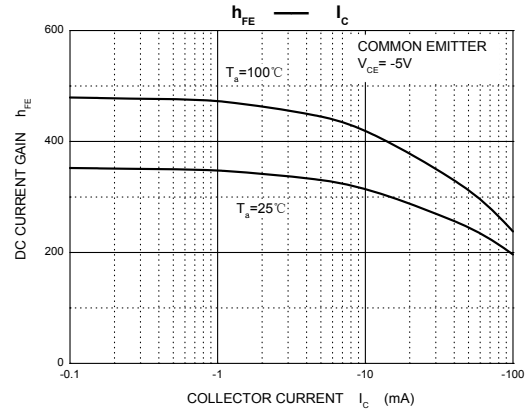
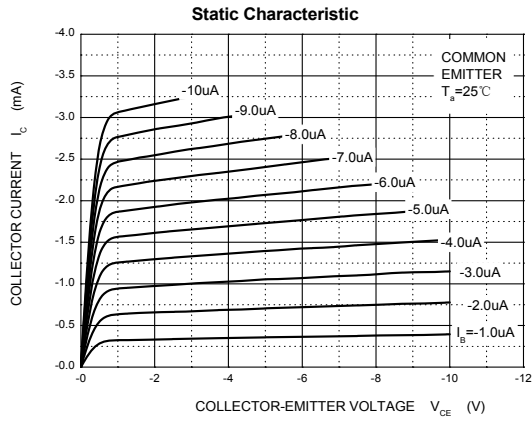
Typical Characteristics

BC846PN/TR1



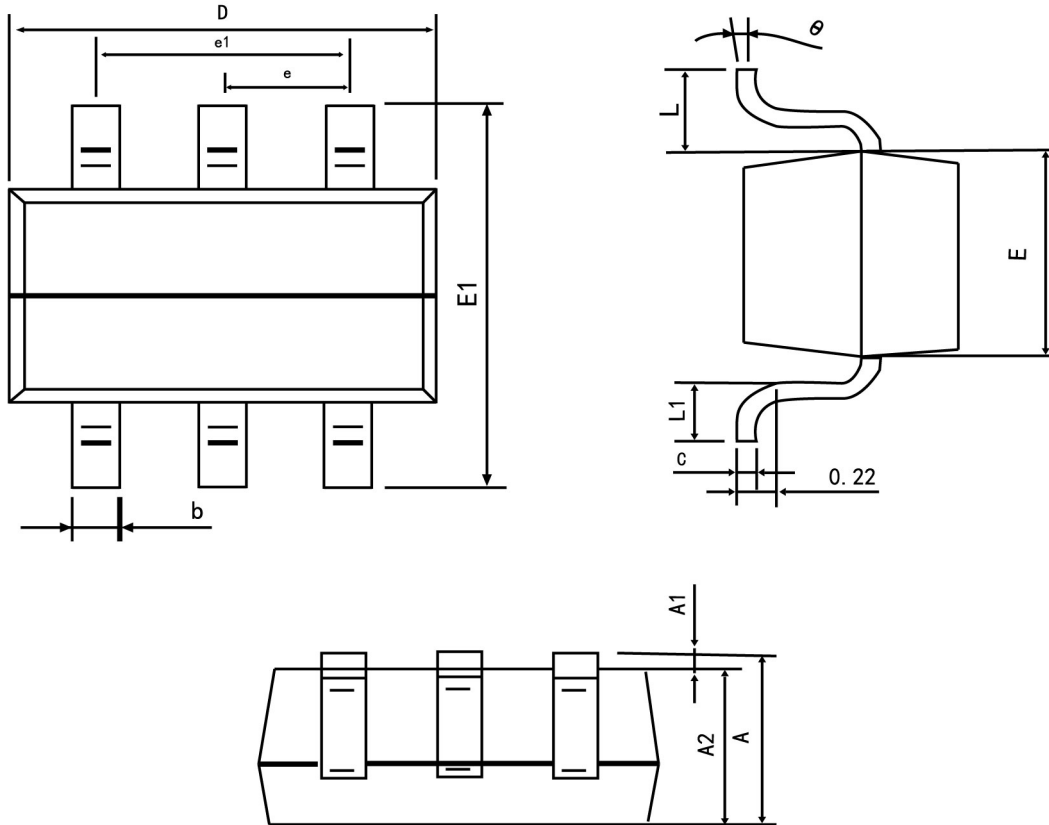
Typical Characteristics

BC846PN/TR2





SOT-363-Package Outline Dimensions



Symbol	Dimension in Millimeters	
	Min	Max
A	0.900	1.100
A1	0.000	0.100
A2	0.900	1.000
b	0.150	0.350
c	0.080	0.150
D	2.000	2.200
E	1.150	1.350
E1	2.150	2.450
e	0.650 TYP	
e1	1.200	1.400
L	0.525 REF	
L1	0.260	0.460
θ	0°	8°